

SKM 600GA126D



SEMITRANS® 4

Trench IGBT Modules

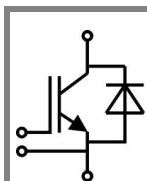
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Features

- Trench = Trenchgate technology
- $V_{CE(sat)}$ with positive temperature coefficient
- High short circuit capability, self limiting to $6 \times I_C$

Typical Applications*

- AC inverter drives
- UPS
- Electronic welders



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Absolute Maximum Ratings		$T_{case} = 25^\circ C$, unless otherwise specified				
Symbol	Conditions	Values			Units	
IGBT						
V_{CES}	$T_j = 25^\circ C$	1200			V	
I_C	$T_j = 150^\circ C$	$T_c = 25^\circ C$	660		A	
		$T_c = 80^\circ C$	460		A	
I_{CRM}	$I_{CRM} = 2 \times I_{Cnom}$	800			A	
V_{GES}		± 20			V	
t_{psc}	$V_{CC} = 600 V$; $V_{GE} \leq 20 V$; $T_j = 125^\circ C$ $V_{CES} < 1200 V$	10			μs	
Inverse Diode						
I_F	$T_j = 150^\circ C$	$T_c = 25^\circ C$	490		A	
		$T_c = 80^\circ C$	340		A	
I_{FRM}	$I_{FRM} = 2 \times I_{Fnom}$	800			A	
I_{FSM}	$t_p = 10 ms$; sin.	$T_j = 150^\circ C$	2900			A
Module						
$I_{t(RMS)}$		500			A	
T_{vj}		-40 ... +150			$^\circ C$	
T_{stg}		-40 ... +125			$^\circ C$	
V_{isol}	AC, 1 min.	4000			V	

Characteristics		$T_{case} = 25^\circ C$, unless otherwise specified				
Symbol	Conditions	min.	typ.	max.	Units	
IGBT						
$V_{GE(th)}$	$V_{GE} = V_{CE}$, $I_C = 16 mA$	5	5,8	6,5	V	
I_{CES}	$V_{GE} = 0 V$, $V_{CE} = V_{CES}$	$T_j = 25^\circ C$	0,2		0,6	mA
		$T_j = 125^\circ C$				mA
V_{CE0}		$T_j = 25^\circ C$	1		1,2	V
		$T_j = 125^\circ C$	0,9		1,1	V
r_{CE}	$V_{GE} = 15 V$	$T_j = 25^\circ C$	1,8		2,4	$m\Omega$
		$T_j = 125^\circ C$	2,8		3,4	$m\Omega$
$V_{CE(sat)}$	$I_{Cnom} = 400 A$, $V_{GE} = 15 V$	$T_j = 25^\circ C_{chiplev.}$	1,7		2,15	V
		$T_j = 125^\circ C_{chiplev.}$	2		2,45	V
C_{ies}	$V_{CE} = 25$, $V_{GE} = 0 V$	$f = 1 MHz$	29		nF	
C_{oes}			1,5		nF	
C_{res}			1,3		nF	
Q_G	$V_{GE} = -8V - +20V$	3600			nC	
R_{Gint}	$T_j = ^\circ C$	1,88			Ω	
$t_{d(on)}$	$R_{Gon} = 2 \Omega$	$V_{CC} = 600V$ $I_C = 400A$	330		ns	
t_r			65		ns	
E_{on}			39		mJ	
$t_{d(off)}$	$R_{Goff} = 2 \Omega$	$T_j = 125^\circ C$ $V_{GE} = \pm 15V$	630		ns	
t_f			130		ns	
E_{off}			64		mJ	
$R_{th(j-c)}$	per IGBT	0,055			K/W	



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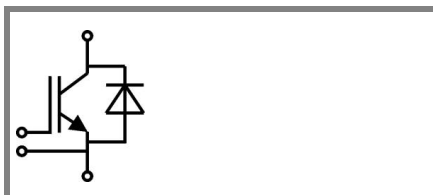
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Characteristics

Symbol	Conditions	min.	typ.	max.	Units	
Inverse diode						
$V_F = V_{EC}$	$I_{Fnom} = 400 \text{ A}; V_{GE} = 0 \text{ V}$		$T_j = 25 \text{ }^\circ\text{C}_{chiplev.}$	1,6	1,8	V
			$T_j = 125 \text{ }^\circ\text{C}_{chiplev.}$	1,6	1,8	V
V_{F0}			$T_j = 25 \text{ }^\circ\text{C}$	1	1,1	V
			$T_j = 125 \text{ }^\circ\text{C}$	0,8	0,9	V
r_F			$T_j = 25 \text{ }^\circ\text{C}$	1,5	1,8	mΩ
			$T_j = 125 \text{ }^\circ\text{C}$	2	2,3	mΩ
I_{RRM}	$I_F = 400 \text{ A}$		$T_j = 125 \text{ }^\circ\text{C}$	350		A
Q_{rr}	$di/dt = 5800 \text{ A}/\mu\text{s}$			87		μC
E_{rr}	$V_{GE} = -15 \text{ V}; V_{CC} = 600 \text{ V}$					mJ
$R_{th(j-c)D}$	per diode			0,125		K/W
Module						
L_{CE}				15	20	nH
$R_{CC'+EE'}$	res., terminal-chip		$T_{case} = 25 \text{ }^\circ\text{C}$	0,18		mΩ
			$T_{case} = 125 \text{ }^\circ\text{C}$	0,22		mΩ
$R_{th(c-s)}$	per module			0,038		K/W
M_s	to heat sink M6			3	5	Nm
M_t	to terminals M6 (M4)			2,5 (1,1)	5 (2)	Nm
w					330	g

This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our personal.

